

-60V P-Channel Power MOSFET

• General Description

It combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- High GOX reliability
- Low Thermal resistance

• Application

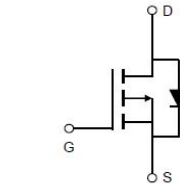
- BLDC Motor driver
- DC-DC
- Load Switch

• Ordering Information:

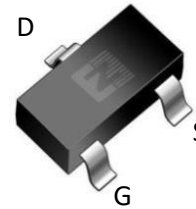
Part NO.	ZMA930P06T
Marking	930P06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		-60	V
Gate-Source Voltage	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	-2.0	A
	I_D	$T_C=75^\circ\text{C}$	-1.98	A
	I_D	$T_C=100^\circ\text{C}$	-1.59	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	-8	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	2	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	0.7	W
Operating Junction Temperature	T_J		-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +150	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, $V_{GS}=-10\text{V}$, $R_g=25\Omega$,	1.2	mJ
		L=0.5mH, $V_{GS}=-10\text{V}$, $R_g=25\Omega$,	2.52	mJ
ESD Level (HBM)	CLASS 2			



$V_{DS} = -60\text{V}$
 $R_{DS(ON)} = 103\text{m}\Omega$
 $I_D = -2\text{A}$



SOT-23-3



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	80	$^{\circ}C/W$
Thermal resistance, junction-ambient ^①	R_{thJA}		-	180	$^{\circ}C/W$
Soldering temperature	T_{sold}		-	260	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1.3	-1.8	-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS} = 0V, V_{DS} = -60V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -1.5A$		103	130	m Ω
		$V_{GS} = -4.5V, I_D = -1A$		128	166	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_{SD} = -1A$		20		S
Diode Forward Voltage	V_{FSD}	$V_{GS} = 0V, I_{SD} = -1.5A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Input capacitance	C_{iss}	$f = 1MHz, V_{DS} = -25V$	-	650	-	pF	
Output capacitance	C_{oss}		-	95	-		
Reverse transfer capacitance	C_{rss}		-	70	-		
Gate Resistance	R_g	$f = 1MHz$	-	8		Ω	
Total gate charge	Q_g	$V_{DD} = -15V, I_D = -1A, V_{GS} = -10V$	-	12	-	nC	
	$Q_g(-4.5v)$		-	21	-		
	Gate - Source charge		Q_{gs}	-	1.6		-
	Gate - Drain charge		Q_{gd}	-	2.6		-
Turn-ON Delay time	$t_{D(on)}$	$V_{GS} = -10V, V_{DS} = -15V, R_G = 3.3\Omega, I_D = -1A$	-	6.5	-	ns	
Turn-ON Rise time	t_r		-	8	-	ns	
Turn-Off Delay time	$t_{D(off)}$		-	16.5	-	ns	
Turn-Off Fall time	t_f		-	4	-	ns	

Fig.1 Gate-Charge Characteristics

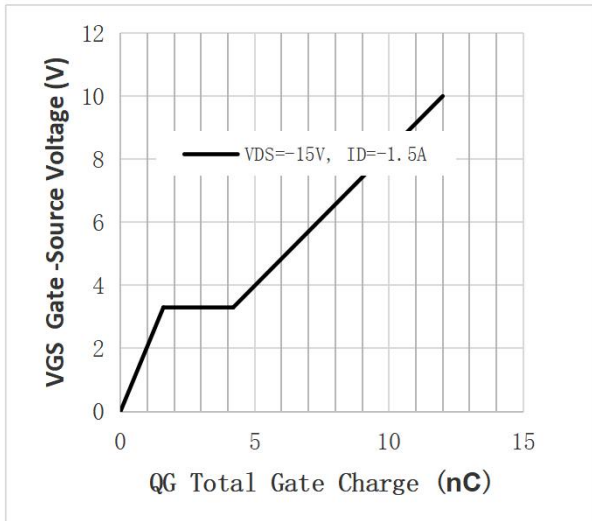


Fig.2 Capacitance Characteristics

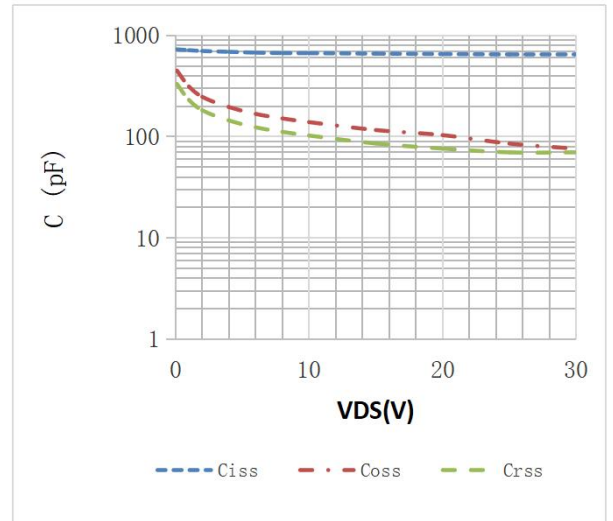


Fig.3 Power Dissipation

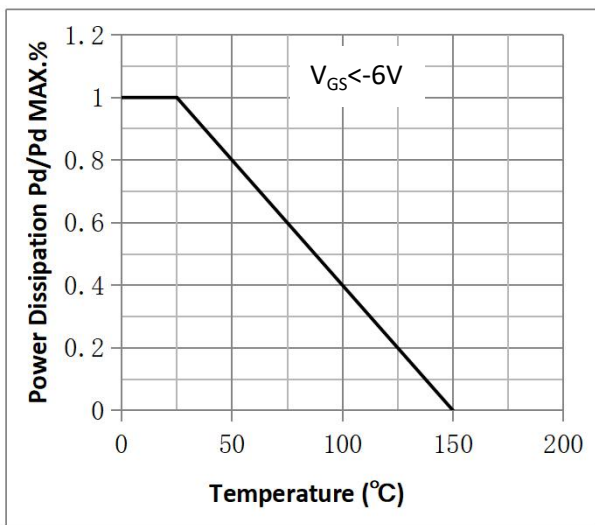


Fig.4 Typical output Characteristics

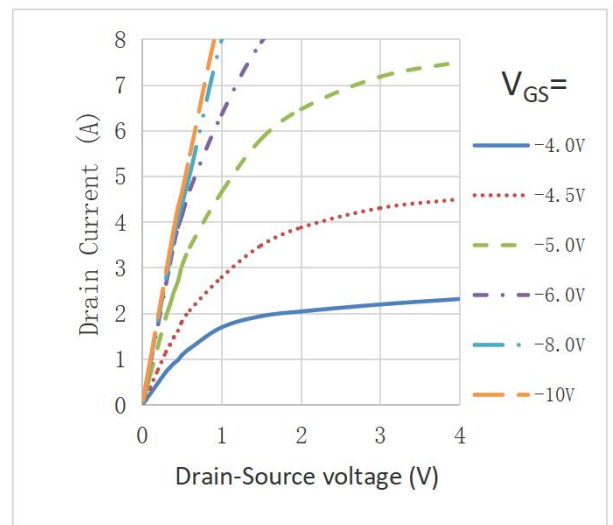


Fig.5 Threshold Voltage V.S Junction Temperature

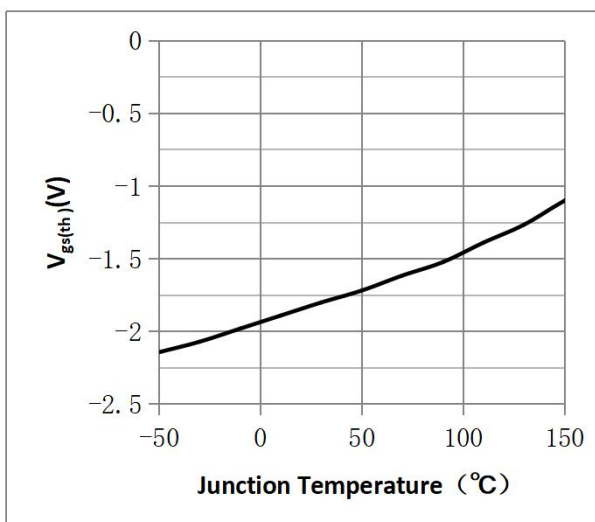


Fig.6 Resistance V.S Drain Current

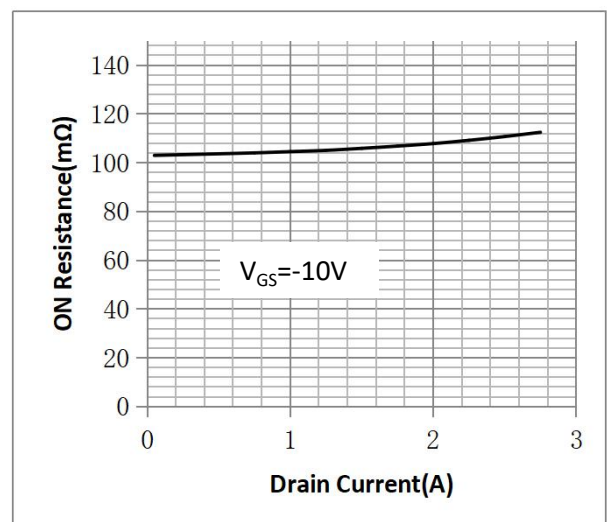


Fig.7 On-Resistance VS Gate Source Voltage

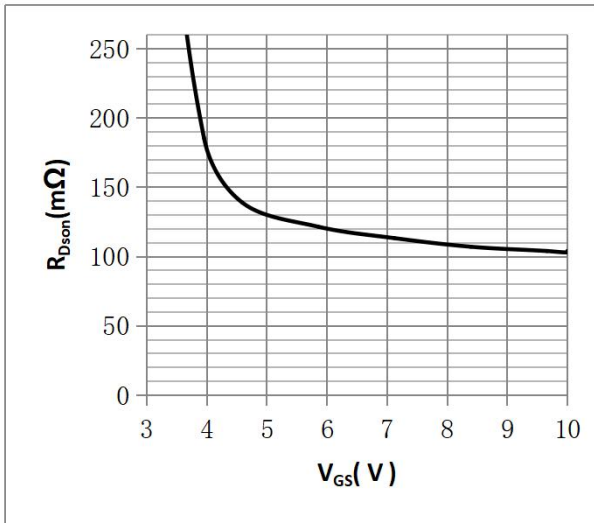


Fig.8 On-Resistance V.S Junction Temperature

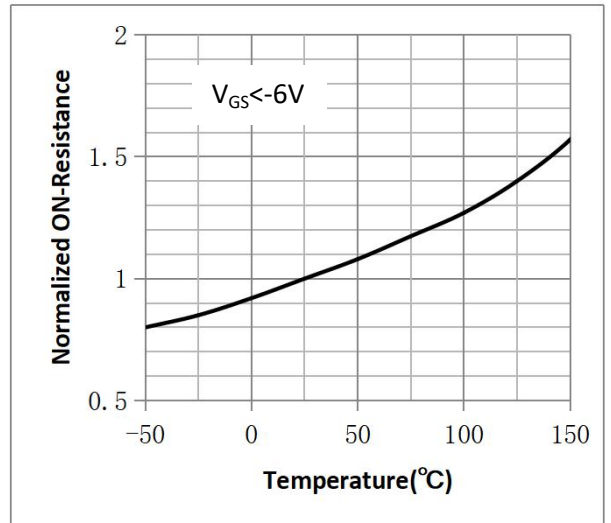


Figure 9. Diode Forward Voltage vs. Current

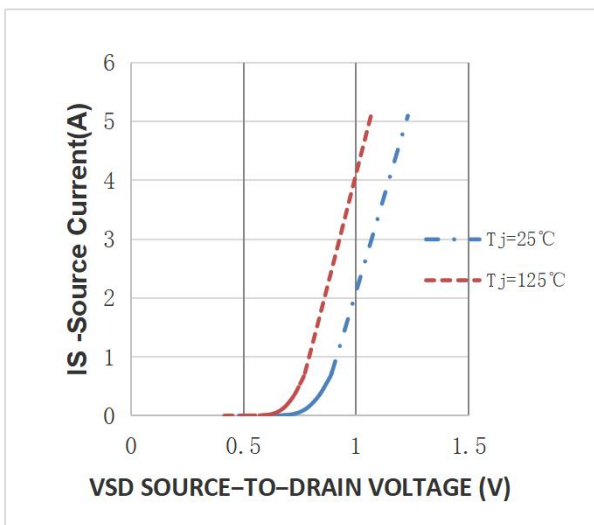


Figure 10. Transfer Characteristics

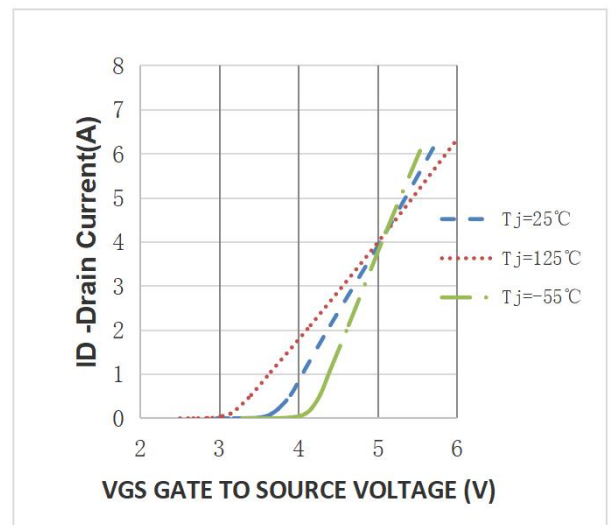


Fig.11 Safe Operating Area

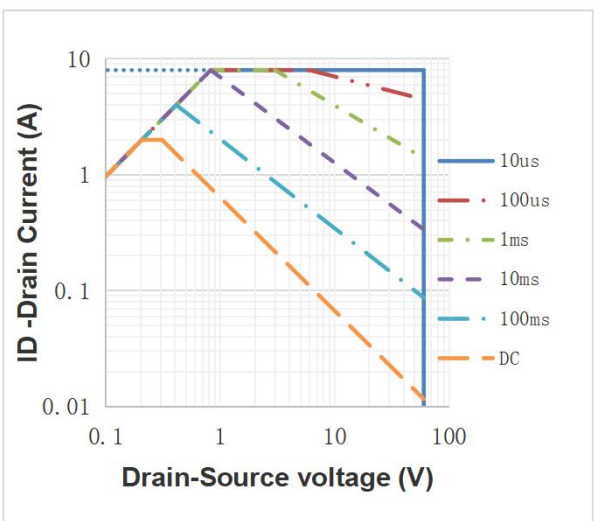
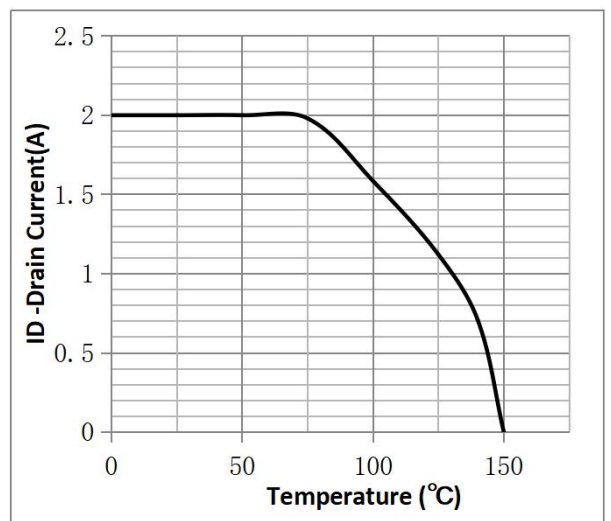
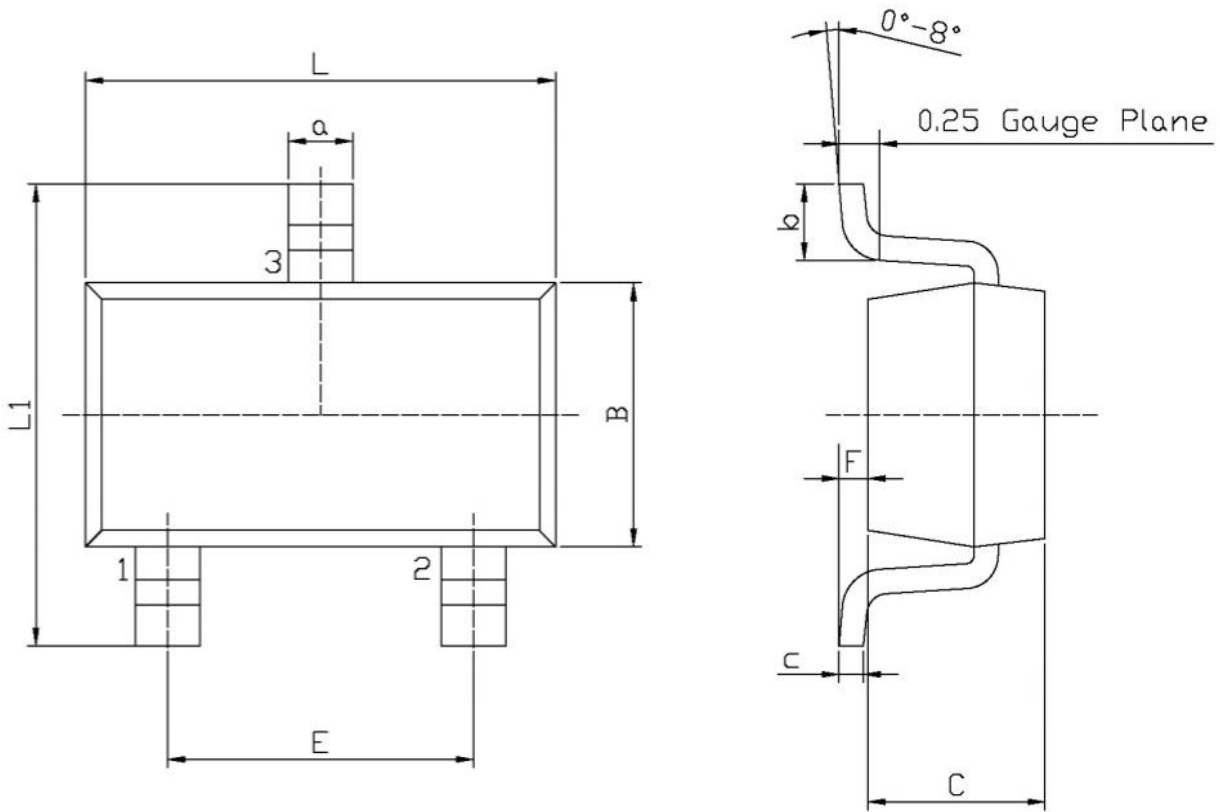


Fig.12 ID vs. Case Temperature[Ⓢ]



•SOT-23-3 Package Outline



Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	a	0.35	0.50
B	1.50	1.70	c	0.10	0.20
C	0.90	1.30	b	0.35	0.55
L1	2.60	3.00	F	0	0.15
E	1.80	2.00			

Note:

- ① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ② Practically the current will be limited by PCB, thermal design and operating temperature. VGS=-10V.

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Revision History

Version	Date	Change
A	2022.1.3	NEW
B	2022.5.7	1.Add Reach, HF figure
C	2022.9.9	1.Add Dynamic characteristics
D	2022.10.30	Add SOA/ID Figure